# 1. General description

NPN low  $V_{\text{CEsat}}$  Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5330PA.

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

### 3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	30	V
I <sub>C</sub>	collector current		-	-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	5	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = 3 A; $I_{B}$ = 300 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02 ; $T_{amb}$ = 25 °C	-	75	100	mΩ



30 V, 3 A NPN low VCEsat (BISS) transistor

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view DFN2020-3 (SOT1061)	2 sym021

# 6. Ordering information

Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PBSS4330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4330PA	AH

30 V, 3 A NPN low VCEsat (BISS) transistor

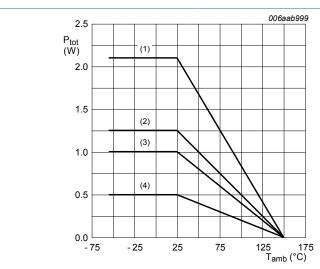
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	30	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	3	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	5	Α
I <sub>B</sub>	base current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, mounting pad for collector 1 cm<sup>2</sup>
- (4) FR4 PCB, standard footprint

#### Fig. 1. Power derating curves

PBSS4330PA

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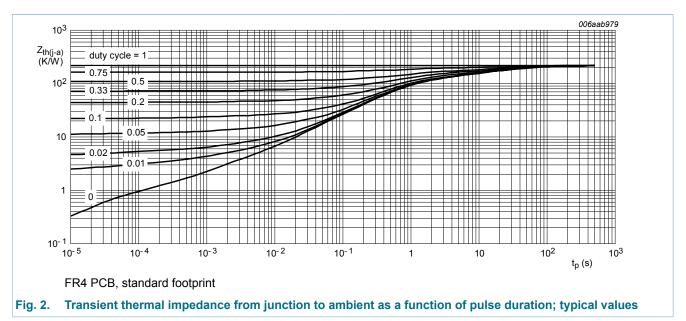
30 V, 3 A NPN low VCEsat (BISS) transistor

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance	ce in free air	[1]	-	-	250	K/W	
	from junction to ambient		[2]	-	-	125	K/W
anbent		[3]	-	-	100	K/W	
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



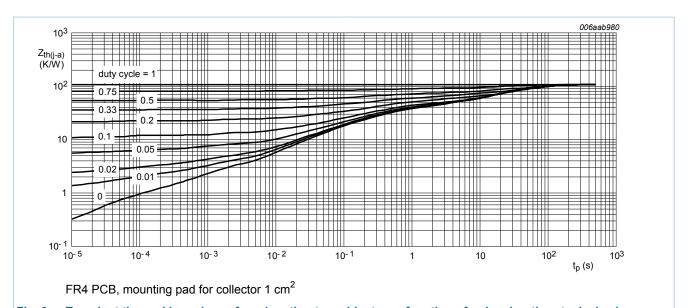


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

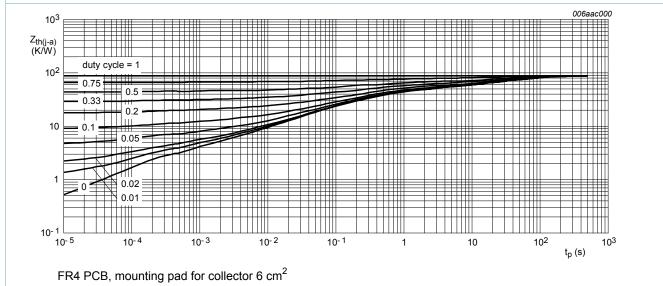
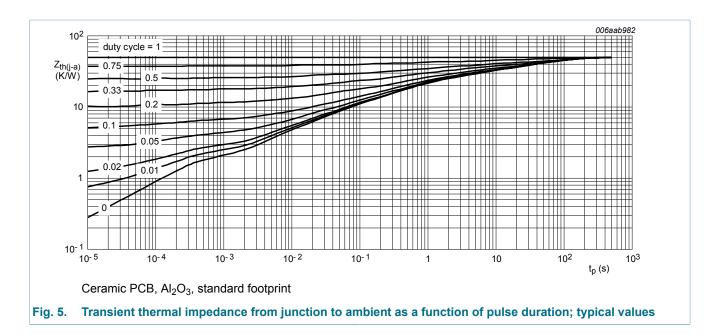


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



30 V, 3 A NPN low VCEsat (BISS) transistor

## 10. Characteristics

Table 7. Characteristics

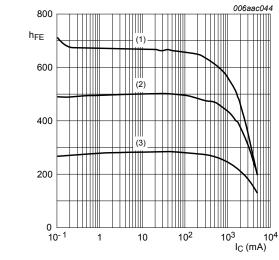
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 24 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 \text{ V; } I_{C} = 0.5 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	300	465	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	270	435	700	
	$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	230	370	-		
	$V_{CE}$ = 2 V; $I_{C}$ = 3 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	180	310	-		
V <sub>CEsat</sub> collector-emitter saturation voltage	$I_{C}$ = 0.5 A; $I_{B}$ = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	40	60	mV	
		$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	80	110	mV
		$I_C$ = 2 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	155	220	mV
		I <sub>C</sub> = 3 A; I <sub>B</sub> = 300 mA; pulsed;	-	220	300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$t_p$ ≤ 300 μs; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	75	100	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 2 A; $I_B$ = 100 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	0.95	1.1	V
		$I_C$ = 3 A; $I_B$ = 300 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	1.07	1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	0.76	1	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 9 V; I <sub>C</sub> = 2 A; I <sub>Bon</sub> = 0.1 A;	-	11	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -0.1 A; T <sub>amb</sub> = 25 °C	-	52	-	ns
ton	turn-on time		-	63	-	ns
s	storage time		-	230	-	ns
t <sub>f</sub>	fall time		-	40	-	ns
$t_{off}$	turn-off time		-	270	-	ns

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### 30 V, 3 A NPN low VCEsat (BISS) transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	210	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	21	30	pF



 $V_{CE} = 2 V$ 

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb}$  = 25 °C

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 6. DC current gain as a function of collector current; typical values

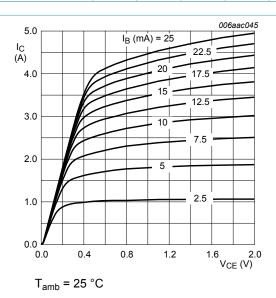
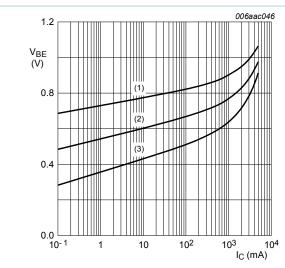


Fig. 7. Collector current as a function of collectoremitter voltage; typical values



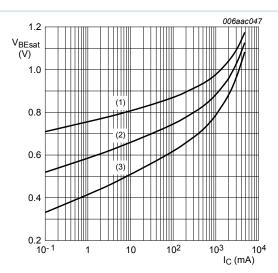
$$V_{CE} = 2 V$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb}$$
 = 100 °C

Fig. 8. Base-emitter voltage as a function of collector current; typical values



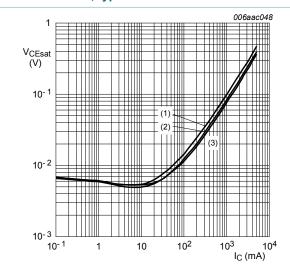
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55$$
 °C

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



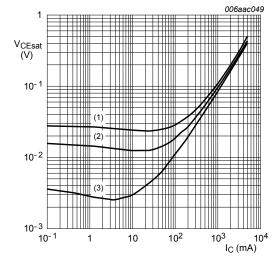
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

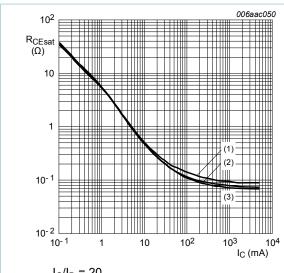


(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



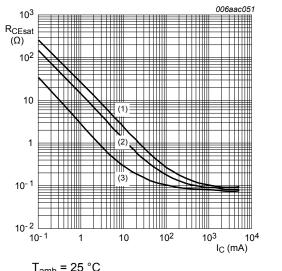
$$I_C/I_B = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1) 
$$I_C/I_B = 100$$

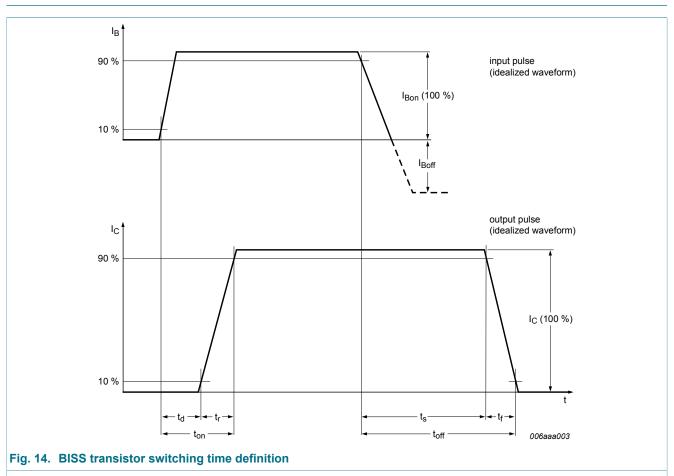
(2) 
$$I_{\rm C}/I_{\rm B} = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values

30 V, 3 A NPN low VCEsat (BISS) transistor

## 11. Test information



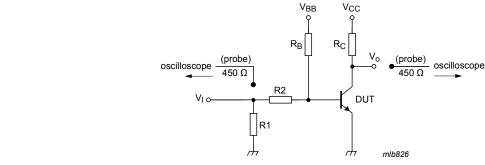
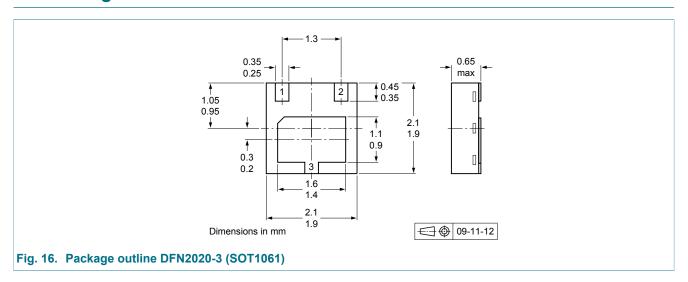


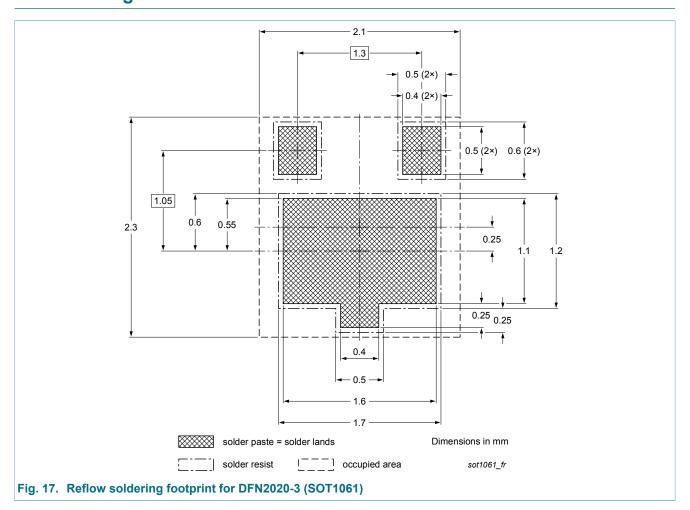
Fig. 15. Test circuit for switching times

30 V, 3 A NPN low VCEsat (BISS) transistor

## 12. Package outline



## 13. Soldering



30 V, 3 A NPN low VCEsat (BISS) transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4330PA v.2	20150407	Product data sheet	-	PBSS4330PA v.1
Modifications:	<ul> <li>Condition V<sub>CE</sub> changed for parameter I<sub>CES</sub> in Table 7, Characteristics</li> </ul>			
PBSS4330PA v.1	20100419	Product data sheet	-	-

#### 30 V, 3 A NPN low VCEsat (BISS) transistor

### 15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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